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# Central<sup>TM</sup> Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

www.centrasemi.com

CS55B  
CS55D

SILICON CONTROLLED RECTIFIER  
0.8 AMPS, 200 AND 400 VOLTS

TO-92 CASE

## DESCRIPTION

The CENTRAL SEMICONDUCTOR CS55B series type are epoxy molded silicon controlled rectifiers designed for applications requiring a low gate sensitivity.

## MAXIMUM RATINGS (T<sub>A</sub>=25°C unless otherwise noted)

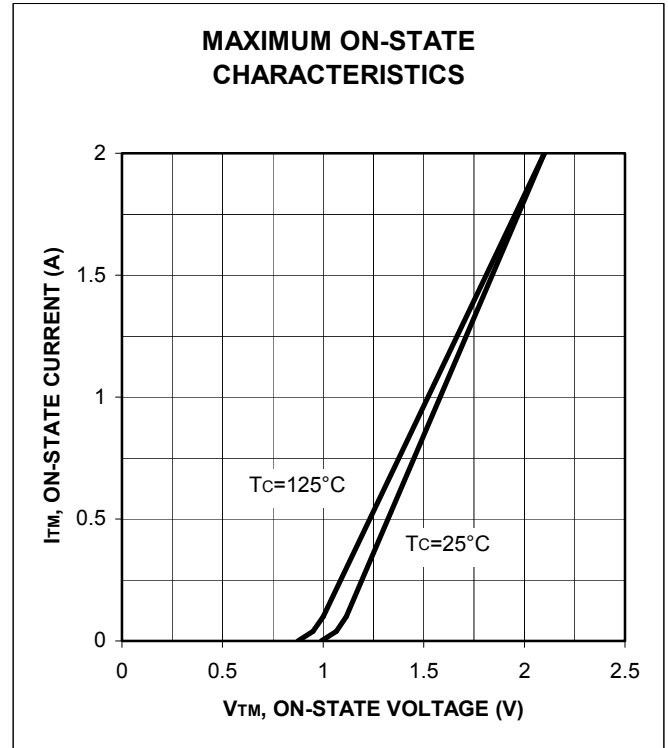
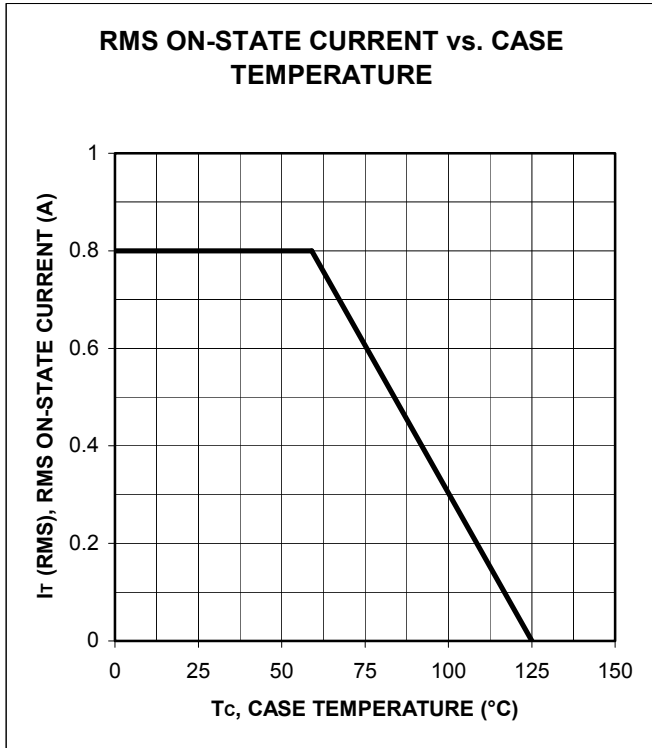
	SYMBOL	CS55B	CS55D	UNITS
Peak Repetitive Off-State Voltage	V <sub>DRM</sub> , V <sub>RRM</sub>	200	400	V
RMS On-State Current (T <sub>C</sub> =60°C)	I <sub>T(RMS)</sub>	0.8		A
Peak One Cycle Surge (t=10ms)	I <sub>TSM</sub>	10		A
I <sup>2</sup> t Value for Fusing (t=10ms)	I <sup>2</sup> t	0.24		A <sup>2</sup> s
Peak Gate Power (tp=10μs)	P <sub>GM</sub>	2.0		W
Average Gate Power Dissipation	P <sub>G(AV)</sub>	0.1		W
Peak Gate Current (tp=10μs)	I <sub>GM</sub>	1.0		A
Peak Gate Voltage (tp=10μs)	V <sub>GM</sub>	8.0		V
Storage Temperature	T <sub>stg</sub>	-40 to +125		°C
Junction Temperature	T <sub>J</sub>	-40 to +125		°C
Thermal Resistance	θ <sub>JA</sub>	200		°C/W
Thermal Resistance	θ <sub>JC</sub>	100		°C/W

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C unless otherwise noted)

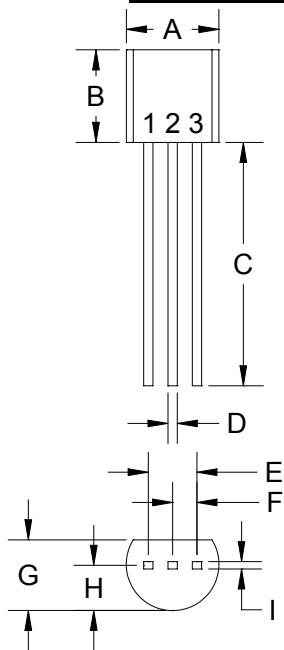
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I <sub>DRM</sub> , I <sub>RRM</sub>	Rated V <sub>DRM</sub> , V <sub>RRM</sub> , R <sub>GK</sub> =1KΩ			1.00	μA
I <sub>DRM</sub> , I <sub>RRM</sub>	Rated V <sub>DRM</sub> , V <sub>RRM</sub> , R <sub>GK</sub> =1KΩ, T <sub>C</sub> =125°C		100		μA
I <sub>GT</sub>	V <sub>D</sub> =12V			200	μA
I <sub>H</sub>	R <sub>GK</sub> =1KΩ			5.00	mA
V <sub>GT</sub>	V <sub>D</sub> =12V			0.8	V
V <sub>TM</sub>	I <sub>TM</sub> =1.0A			1.70	V
dv/dt	V <sub>D</sub> =.67 x V <sub>DRM</sub> , R <sub>GK</sub> =1KΩ, T <sub>C</sub> =125°C	25			V/μs

(SEE REVERSE SIDE)

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### TO-92 PACKAGE - MECHANICAL OUTLINE



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.175	0.205	4.45	5.21
B	0.170	0.210	4.32	5.33
C	0.500	-	12.70	-
D	0.016	0.022	0.41	0.56
E	0.100		2.54	
F	0.050		1.27	
G	0.125	0.165	3.18	4.19
H	0.080	0.105	2.03	2.67
I	0.015		0.38	

TO-92 (REV: R1)

Lead Code: 1) Anode  
2) Gate  
3) Cathode

R1

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